

SPECIFICATION OF LED CHIP

C680-35

[INFRARED]

1) Commodity Type and Physical Characteristics.

- 1. Material GaAlAs
- 2. Electrode Top Side N (cathode) side : Au Alloy & Pad
Bottom Side P (anode) side : Au Alloy
- 3. Electrode Pattern Fig.1
- 4. Chip Size Fig.2
- 5. Chip Thickness Fig.2
- 6. Emission Area Fig.2

2) Electro-Optical Characteristics [Ta=25°C]

| Parameters | Symbol | Condition | min. | typ. | max. | Unit |
|------------------------------|-----------------|-----------|------|------|------|------|
| Forward Voltage | Vf | If=20mA | | 1.8 | 2.2 | V |
| Reverse Current | Ir | Vr=5V | | | 10 | uA |
| Power Intensity | Po | If=20mA | 1.0 | 2.0 | | mW |
| Peak Wavelength | λ_P | If=20mA | 670 | 680 | 690 | nm |
| Spectral Radiation Bandwidth | $\Delta\lambda$ | If=20mA | | 20 | | nm |
| Rise Time | tr | If=20mA | | 80 | | ns |
| Full time | tf | If=20mA | | 80 | | ns |

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

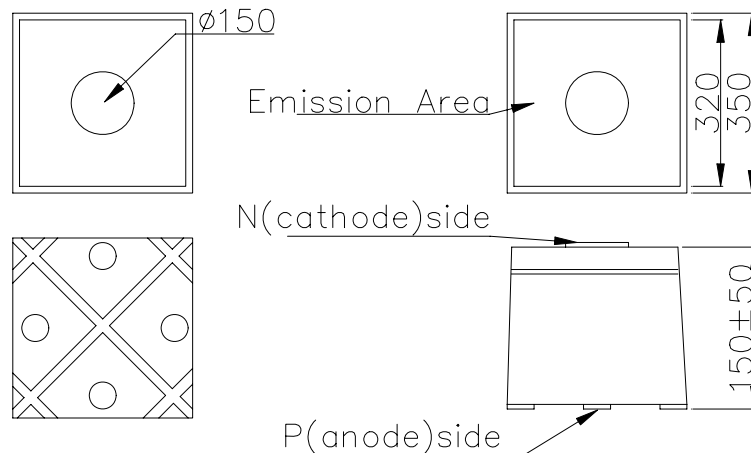


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area